

Accepted Manuscript

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PII: S0022-0248(18)30405-6

DOI: <https://doi.org/10.1016/j.jcrysgr.2018.08.025>

Reference: CRYG 24716

To appear in: *Journal of Crystal Growth*

Received Date: 14 March 2018

Revised Date: 21 August 2018

Accepted Date: 22 August 2018



Please cite this article as: E. Letts, Y. Sun, D. Key, B. Jordan, T. Hashimoto, X-ray characterization technique for the assessment of surface damage in GaN wafers, *Journal of Crystal Growth* (2018), doi: <https://doi.org/10.1016/j.jcrysgr.2018.08.025>

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X-ray characterization technique for the assessment of surface damage in GaN wafers

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SixPoint Materials has successfully switched to production of two-inch diameter GaN wafers using the ammonothermal method. Crystal quality values are high with dislocation densities typically in the low 10^5 cm^{-2} . In efforts to produce true epi-ready material, investigations were made to develop a technique to study surface damage caused by the back-end process using X-ray diffraction methods. Analysis of peak tailing from X-ray rocking curves of the (114) reflection indicates the progression of surface damage during each step of the back-end process. For instance, the tailing can be partially represented using full width five thousand max (FW5000M) values. By using a peak with a low glancing angle, such as the (114) reflection's angle of 10.8662° , more of the X-ray beam is scattered in the surface region, providing an improved measurement of surface damage. Since this technique is non-destructive and can be performed without dismounting the sample from its ceramic back-end processing plate, it can provide information on the damaged layer at each stage of the back-end process. Using this technique to evaluate samples from various manufacturers, we found a lack of uniformity in surface damage from GaN companies. It is our hope that this technique will be adopted to better standardize surface damage measurements in the GaN field.

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PACS codes: 8233.De, 81.05.EA, 81.10.Dn

Keywords: A1. Surface processes; A1. X-ray diffraction; A2. Growth from solutions; A2. Single crystal growth; B1. Nitrides; B2. Semiconducting gallium compounds

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